

isc Silicon NPN Power Transistor

BU706F

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 700V(\text{Min})$
- High Switching Speed

APPLICATIONS

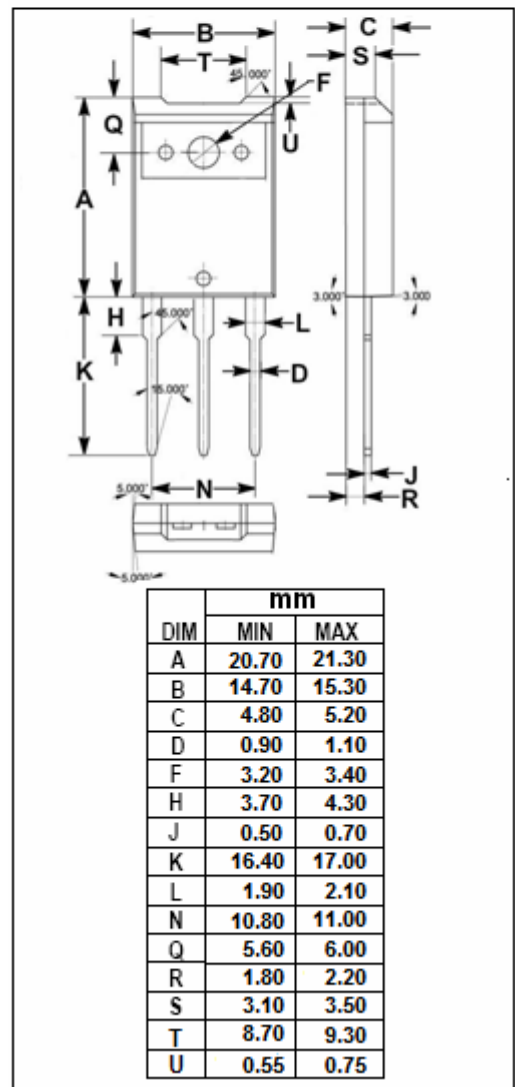
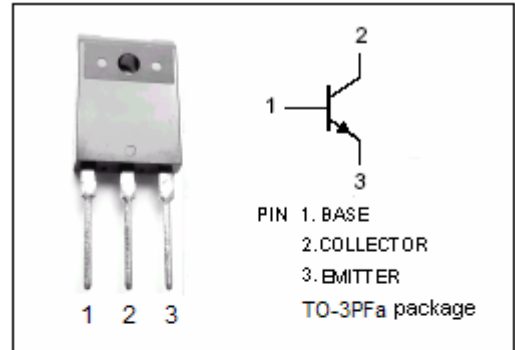
- Designed for use in horizontal deflection circuits of color TV receivers and line operated switch-mode applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage $V_{BE}=0$	1500	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	3	A
I_{BM}	Base Current-Peak	5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	32	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.95	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	35	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.1\text{A}; I_B=0; L=25\text{mH}$	700			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=1.33\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=1.33\text{A}$			1.3	V
I_{CES}	Collector Cutoff Current	$V_{CE}=V_{CESmax}; V_{BE}=0$ $V_{CE}=V_{CESmax}; V_{BE}=0; T_J=125^{\circ}\text{C}$			0.5 1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			10	mA
h_{FE}	DC Current Gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	2.25			
$I_{S/B}$	Second Breakdown Current	$V_{CE}=300\text{V}; t_p=200\mu\text{s}$	1.0			A

Switching Times

t_f	Fall Time	$I_C=3\text{A}; I_{B(end)}=1\text{A}; L_B=12\mu\text{H}$		0.7		μs
t_s	Storage Time			6.5		μs